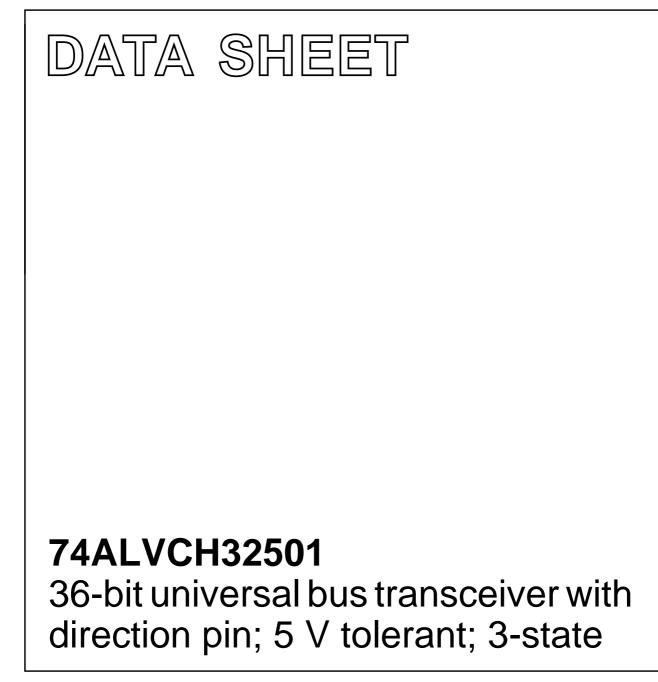
INTEGRATED CIRCUITS



Product specification File under Integrated Circuits, IC24 2000 Mar 16



FEATURES

- 3-state non-inverting outputs for bus oriented applications
- Wide supply voltage range of 1.2 to 3.6 V
- Complies with JEDEC standard no. 8-1A
- Current drive ±24 mA at 3.0 V
- Universal bus transceiver with D-type latches and D-type flip-flops capable of operating in transparent, latched or clocked mode
- CMOS low power consumption
- Direct interface with TTL levels
- · All inputs have bus-hold circuitry
- Output drive capability 50 Ω transmission lines at 85 °C
- Plastic fine-pitch ball grid array package.

DESCRIPTION

The 74ALVCH32501 is a high-performance CMOS product designed for V_{CC} operation at 2.5 and 3.3 V with I/O compatibility up to 5 V.

Active bus-hold circuitry is provided to hold unused or floating data inputs at a valid logic level.

QUICK REFERENCE DATA

GND = 0 V; T_{amb} = 25 °C; t_r = $t_f \le$ 2.5 ns.

The 74ALVCH32501 can be used as two 18-bit transceivers or one 36-bit transceiver featuring non-inverting 3-state bus compatible outputs in both send and receive directions. Data flow in each direction is controlled by output enable (OE_{AB} and \overline{OE}_{BA}), latch enable (LE_{AB} and LE_{BA}), and clock inputs (CP_{AB} and CP_{BA}). For A-to-B data flow, the device operates in the transparent mode when LE_{AB} is HIGH. When input LE_{AB} is LOW, the A data is latched if input CP_{AB} is held at a HIGH or LOW level. If input LE_{AB} is LOW, the A data is stored in the latch/flip-flop on the LOW-to-HIGH transition of CP_{AB} . When input OE_{AB} is HIGH, the outputs are active. When input OE_{AB} is LOW, the outputs are in the high-impedance state.

Data flow for B-to-A is similar to that of A-to-B, but uses inputs \overline{OE}_{BA} , LE_{BA} and CP_{BA}. The output enables are complimentary (OE_{AB} is active HIGH, and \overline{OE}_{BA} is active LOW).

To ensure the high-impedance state during power-up or power-down, pin \overline{OE}_{BA} should be tied to V_{CC} through a pull-up resistor and pin OE_{AB} should be tied to GND through a pull-down resistor. The minimum value of the resistor is determined by the current-sinking or current-sourcing capability of the driver.

SYMBOL	PARAMETER	CONDITIONS	TYP.	UNIT
t _{PHL} /t _{PLH}	propagation delay A_n to B_n ; B_n to A_n	$C_{L} = 30 \text{ pF}; V_{CC} = 2.5 \text{ V}$	2.8	ns
		$C_L = 50 \text{ pF}; V_{CC} = 3.3 \text{ V}$	3.0	ns
CI	input capacitance		4.0	pF
C _{I/O}	input/output capacitance		8.0	pF
C _{PD}	power dissipation capacitance per latch	$V_I = GND$ to V_{CC} ; note 1		
		outputs enabled	21	pF
		outputs disabled	3	pF

Note

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i + \Sigma (C_L \times V_{CC}^2 \times f_o)$ where:

 f_i = input frequency in MHz;

 $f_o = output frequency in MHz;$

 C_L = output load capacitance in pF;

V_{CC} = supply voltage in Volts;

 $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

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FUNCTION TABLE

See notes 1 and 2.

	INF	TUT		INTERNAL	OUTPUT	
nOE _{AB}	nLE _{AB}	nCP _{AB}	nA _n	REGISTERS	nB _n	OPERATING MODE
L	Н	Х	Х	Х	Z	disabled
L	\downarrow	Х	h	Н	Z	disabled; latch data
L	\downarrow	Х	I	L	Z	
L	L	H or L	Х	NC	Z	disabled; hold data
L	L	\uparrow	h	Н	Z	disabled; clock data
L	L	\uparrow	I	L	Z	
Н	Н	Х	Н	Н	Н	transparent
н	Н	Х	L	L	L	
Н	\downarrow	Х	h	Н	Н	latch data and display
н	\downarrow	Х	I	L	L	
Н	L	\uparrow	h	Н	Н	clock data and display
н	L	\uparrow	I	L	L	
Н	L	H or L	Х	Н	Н	hold data and display
Н	L	H or L	Х	L	L	

Notes

1. A-to-B data flow is shown; B-to-A flow is similar but uses $n\overline{OE}_{BA}$, nLE_{BA} and nCP_{BA} .

2. H = HIGH voltage level;

h = HIGH voltage level on set-up time prior to the enable or clock transition;

L = LOW voltage level;

I = LOW voltage level on set-up time prior to the enable or clock transition;

NC = no change;

X = don't care;

- \uparrow = LOW-to-HIGH enable or clock transition;
- \downarrow = HIGH-to-LOW enable or clock transition;
- Z = high impedance OFF-state.

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ORDERING INFORMATION

			PACKAGE		
TYPE NUMBER	TEMPERATURE RANGE	PINS	PACKAGE	MATERIAL	CODE
74ALVCH32501EC	–40 to +85 °C	114	LFBGA114	plastic	SOT537-1

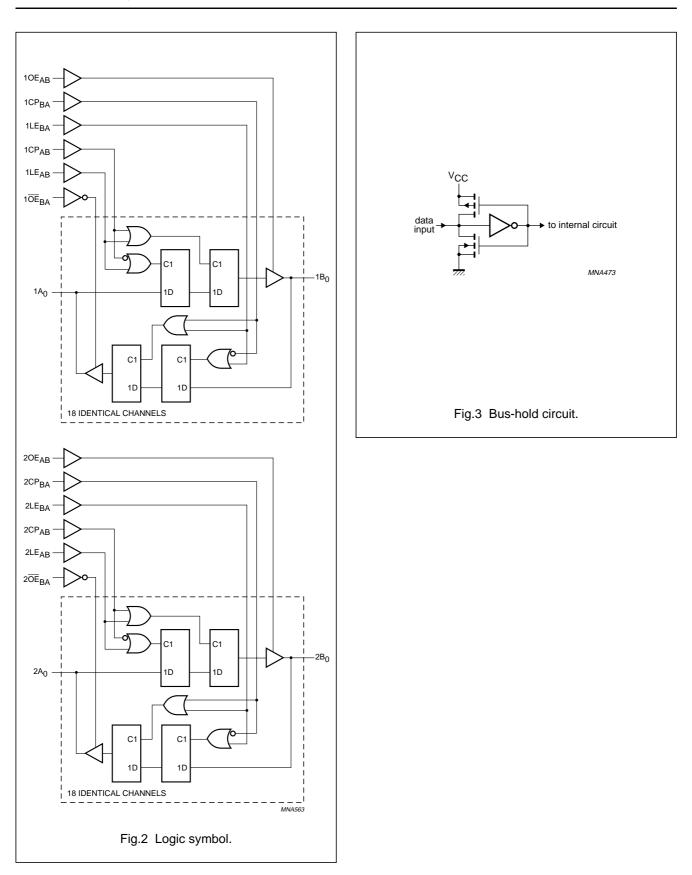
PINNING

SYMBOL	DESCRIPTION
nA _n	data inputs
nB _n	data outputs
GND	ground (0 V)
V _{CC}	DC supply voltage
nOE _{AB}	output enable inputs A to B (active HIGH)
nOE _{BA}	output enable inputs B to A (active LOW)
nLE _{AB}	latch enable inputs A to B
nLE _{BA}	latch enable inputs B to A
nCP _{AB}	clock input A to B
nCP _{BA}	clock input B to A

6	1B ₁	1B3	1B ₅	1B ₇	1B ₉	1B ₁₁	1B ₁₃	1B ₁₄	1B ₁₆	n.c.	2B ₁	2B3	2B5	2B7	2B9	2B ₁₁	2B ₁₃	2B14	2B ₁₆
5	1B ₀	1B ₂	1B ₄	1B ₆	1B ₈	1B ₁₀	1B ₁₂	1B ₁₅	1B ₁₇	2CP _{AB}	2B ₀	28 ₂	2B ₄	2B ₆	28 ₈	2B ₁₀	2B ₁₂	2B ₁₅	2B ₁₇
4	1CP _{AB}	GND	GND	VCC	GND	GND	Vcc	GND	1CP _{BA}	GND	GND	GND	v _{cc}	GND	GND	Vcc	GND	2CPBA	GND
3	1LE _{AB}	10E _{AB}	GND	VCC	GND	GND	Vcc	GND		1LE _{BA}	20E _{AB}	GND	v _{cc}	GND	GND	v _{cc}	GND		2LE _{BA}
2	1A ₀	1A ₂	1A ₄	1A ₆	1A ₈	1A ₁₀	1A ₁₂	1A ₁₅	1A ₁₇	2LE _{AB}	2A ₀	2A ₂	2A4	2A ₆	2A8	2A ₁₀	2A ₁₂	2A ₁₅	2A ₁₇
1	1A ₁	1A ₃	1A ₅	1A ₇	1Ag	1A ₁₁	1A ₁₃	1A ₁₄	1A ₁₆	n.c.	2A ₁	2A3	2A5	2A7	2A9	2A ₁₁	2A ₁₃	2A ₁₄	2A ₁₆
	A	В	С	D	E	F	G	н	J	к	L	М	N	Р	R	т	U	V	w

Fig.1 Pin configuration.

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RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CC}	DC supply voltage	2.5 V range (for maximum speed performance at 30 pF output load)	2.3	2.7	V
		3.3 V range (for maximum speed performance at 50 pF output load)	3.0	3.6	V
VI	DC input voltage		0	V _{CC}	V
Vo	DC output voltage	output HIGH or LOW state	0	V _{CC}	V
T _{amb}	ambient temperature		-40	+85	°C
t _r , t _f	input rise and fall time ratios	V _{CC} = 1.2 to 2.7 V	0	20	ns/V
	$(\Delta t/\Delta V)$	V _{CC} = 2.7 to 3.6 V	0	10	ns/V

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134); voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CC}	DC supply voltage		-0.5	+4.6	V
VI	DC input voltage	for control pins; note 1	-0.5	+4.6	V
		for data input pins; note 1	-0.5	V _{CC} + 0.5	V
I _{IK}	DC input diode current	V ₁ < 0	-	-50	mA
I _{OK}	DC output clamping diode current	V _O < 0; note 1	-	50	mA
Vo	DC output voltage	see note 1	-0.5	V _{CC} + 0.5	V
lo	DC output sink current	$V_{O} = 0$ to V_{CC}	-	-50	mA
I _{CC} , I _{GND}	DC V_{CC} or GND current		_	±100	mA
T _{stg}	storage temperature		-65	+150	°C
P _D	power dissipation per packages	for temperature range: -40 to +85 °C; note 2	_	1000	mW

Notes

- 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
- 2. Above 55 °C the value of P_D derates linearly with 1.8 mW/K.

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DC CHARACTERISTICS

Over recommended operating conditions; voltages are referenced to GND (ground = 0 V).

		TEST CONDITIO	NS		T _{amb} (°C)			
SYMBOL	PARAMETER				–40 to +85			
		OTHER	V _{CC} (V)	MIN.	TYP. ⁽¹⁾	MAX.	1	
VIH	HIGH-level input		2.3 to 2.7	1.7	1.2	_	V	
	voltage		2.7 to 3.6	2.0	1.5	-	V	
V _{IL}	LOW-level input		2.3 to 2.7	-	1.2	0.7	V	
	voltage		2.7 to 3.6	-	1.5	0.8	V	
V _{OH}	HIGH-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$						
	voltage	I _O = -100 μA	2.3 to 3.6	V _{CC} - 0.2	V _{CC}	_	V	
		$I_0 = -6 \text{ mA}$	2.3	$V_{CC} - 0.3$	V _{CC} - 0.08	_	V	
		I _O = -12 mA	2.3	V _{CC} - 0.6	V _{CC} - 0.26	_	V	
		I _O = -12 mA	2.7	$V_{CC} - 0.5$	V _{CC} - 0.14	-	V	
		$I_0 = -12 \text{ mA}$	3.0	$V_{CC} - 0.6$	V _{CC} - 0.09	_	V	
		I _O = -24 mA	3.0	V _{CC} – 1.0	V _{CC} - 0.28	-	V	
V _{OL}	LOW-level output	$V_{I} = V_{IH} \text{ or } V_{IL}$						
	voltage	I _O = 100 μA	2.3 to 3.6	_	GND	0.20	V	
		I _O = 6 mA	2.3	-	0.07	0.40	V	
		I _O = 12 mA	2.3	_	0.15	0.70	V	
		I _O = 12 mA	2.7	_	0.14	0.40	V	
		I _O = 24 mA	3.0	-	0.27	0.55	V	
l	input leakage current	$V_{I} = V_{CC}$ or GND	2.3 to 3.6	-	±0.1	±5	μA	
I _{OZ}	3-state output OFF-state current	$V_{I} = V_{IH} \text{ or } V_{IL};$ $V_{O} = V_{CC} \text{ or GND; note 2}$	2.3 to 3.6	-	0.1	±10	μA	
I _{CC}	quiescent supply current	$V_{I} = V_{CC}$ or GND; $I_{O} = 0$	2.3 to 3.6	-	0.4	80	μA	
ΔI _{CC}	additional quiescent supply current given per data I/O pin with bus-hold	$V_{I} = V_{CC} - 0.6 \text{ V}; I_{O} = 0$	2.7 to 3.6	_	150	750	μA	
I _{BHL}	bus-hold LOW	V _I = 0.7 V; note 3	2.3	45	_	-	μA	
	sustaining current	V _I = 0.8 V; note 3	3.0	75	150	_	μA	
I _{BHH}	bus-hold HIGH	V _I = 1.7 V; note 3	2.3	-45	_	-	μA	
	sustaining current	V _I = 2.0 V; note 3	3.0	-75	-175	_	μA	
I _{BHLO}	bus-hold LOW overdrive current	note 3	3.6	500	-	-	μA	
I _{BHHO}	bus-hold HIGH overdrive current	note 3	3.6	-500	-	-	μA	

Notes

1. All typical values are at V_{CC} = 3.3 V and T_{amb} = 25 °C.

2. For I/O ports, the parameter I_{OZ} includes the input leakage current.

3. Valid for data inputs of bus-hold parts.

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AC CHARACTERISTICS

GND = 0 V

SAMBO	DADAMETED	TEST CONDIT	T _{amb} :				
SYMBOL	PARAMETER	WAVEFORMS	CL	MIN.	TYP.	MAX.	
$V_{\rm CC} = 2.3 \ {\rm tc}$	o 2.7 V; t_r = t_f ≤ 2.0 ns; note 1	·					
t _{PHL} /t _{PLH}	propagation delay						
	nA _n to nB _n ; nB _n to nA _n	see Figs 4 and 8	30 pF	1.0	2.8	5.1	ns
	nLE _{BA} to nA _n ; nLE _{AB} to nB _n	see Figs 5 and 8		1.1	3.5	6.1	ns
	nCP _{BA} to nA _n ; nCP _{AB} to nB _n	see Figs 5 and 8		1.0	3.3	6.1	ns
t _{PZH} /t _{PZL}	3-state output enable time nOE _{AB} to nB _n	see Figs 6 and 8		1.0	2.5	5.8	ns
	3-state output enable time $n\overline{OE}_{BA}$ to nA_n	see Figs 6 and 8		1.3	2.8	6.3	ns
t _{PHZ} /t _{PLZ}	3-state output disable time nOE _{AB} to nB _n	see Figs 6 and 8		1.5	2.5	6.2	ns
	3-state output disable time $n\overline{OE}_{BA}$ to nA_n	see Figs 6 and 8		1.3	2.5	5.3	ns
t _W	nLE _{AB} or nLE _{BA} pulse width HIGH	see Figs 5 and 8		3.3	0.8	_	ns
	nCP _{AB} or nCP _{BA} pulse width HIGH or LOW	see Figs 5 and 8		3.3	2.0	-	ns
t _{su}	set-up time nA_n before nCP_{AB}^{\uparrow} or nB_n before nCP_{BA}^{\uparrow}	see Figs 7 and 8		1.7	0.1	-	ns
	set-up time CP HIGH or LOW nA_n before $nLE_{AB}\downarrow$ or nB_n before $nLE_{BA}\downarrow$	see Figs 7 and 8		1.1	0.1	-	ns
t _h	hold time nA_n after nCP_{AB}^{\uparrow} or nB_n after nCP_{BA}^{\uparrow}	see Figs 7 and 8		1.7	0.3	-	ns
	hold time CP HIGH or LOW nA_n after $nLE_{AB}\downarrow$ or nB_n after $nLE_{BA}\downarrow$	see Figs 7 and 8		1.6	0.3	-	ns
f _{max}	maximum clock frequency	see Figs 5 and 8		150	330	_	MHz
$V_{CC} = 2.7 V$; t _r = t _f ≤ 2.5 ns ; note 2	·					
t _{PHL} /t _{PLH}	propagation delay						
	nA _n to nB _n ; nB _n to nA _n	see Figs 4 and 8	50 pF	_	3.0	4.6	ns
	nLE_{BA} to nA_n ; nLE_{AB} to nB_n	see Figs 5 and 8		_	3.6	5.3	ns
	nCP_{BA} to nA_n ; nCP_{AB} to nB_n	see Figs 5 and 8		_	3.4	5.6	ns
t _{PZH} /t _{PZL}	3-state output enable time nOE _{AB} to nB _n	see Figs 6 and 8	1	_	2.7	5.3	ns
	3-state output enable time $n\overline{OE}_{BA}$ to nA_n	see Figs 6 and 8	1	_	3.3	6.0	ns
t _{PHZ} /t _{PLZ}	3-state output disable time nOE _{AB} to nB _n	see Figs 6 and 8	1	_	3.6	5.7	ns
	3-state output disable time $n\overline{OE}_{BA}$ to nA_n	see Figs 6 and 8	1	_	3.3	4.6	ns
t _W	pulse width nLE _{AB} or nLE _{BA} HIGH	see Figs 5 and 8	1	3.3	0.7	-	ns
	pulse width nCP _{AB} or nCP _{BA} HIGH or LOW	see Figs 5 and 8		3.3	1.4	-	ns

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CVMDO!		TEST CONDIT	T _{amb} :	= –40 to	+85 °C		
SYMBOL	PARAMETER	WAVEFORMS	CL	MIN.	TYP.	MAX.	
t _{su}	set-up time nA_n before nCP_{AB}^{\uparrow} or nB_n before nCP_{BA}^{\uparrow}	see Figs 7 and 8	50 pF	+1.4	-0.1	-	ns
	set-up time CP HIGH or LOW nA_n before $nLE_{AB}\downarrow$ or nB_n before $nLE_{BA}\downarrow$	see Figs 7 and 8		+1.0	-0.2	-	ns
t _h	hold time nA_n after nCP_{AB}^{\uparrow} or nB_n after nCP_{BA}^{\uparrow}	see Figs 7 and 8		1.6	0.3	-	ns
	hold time CP HIGH or LOW nA_n after $nLE_{AB}\downarrow$ or nB_n after $nLE_{BA}\downarrow$	see Figs 7 and 8		1.5	0.1	-	ns
f _{max}	maximum clock frequency	see Figs 5 and 8		150	333	-	MHz
$V_{CC} = 3.0$ to	9 3.6 V; $\mathbf{t}_r = \mathbf{t}_f \le$ 2.5 ns; note 3						
t _{PHL} /t _{PLH}	propagation delay						
	nA _n to nB _n ; nB _n to nA _n	see Figs 4 and 8	50 pF	1.0	3.0	4.2	ns
	nLE_{BA} to nA_n ; nLE_{AB} to nB_n	see Figs 5 and 8		1.3	3.4	4.8	ns
	nCP _{BA} to nA _n ; nCP _{AB} to nB _n	see Figs 5 and 8		1.4	3.3	4.9	ns
t _{PZH} /t _{PZL}	3-state output enable time nOE _{AB} to nB _n	see Figs 6 and 8		1.0	2.4	4.6	ns
	3-state output enable time $n\overline{OE}_{BA}$ to nA_n	see Figs 6 and 8	1	1.1	2.5	5.0	ns
t _{PHZ} /t _{PLZ}	3-state output disable time nOE _{AB} to nB _n	see Figs 6 and 8		1.4	2.9	5.0	ns
	3-state output disable time $n\overline{OE}_{BA}$ to nA_n	see Figs 6 and 8		1.3	3.1	4.2	ns
t _W	pulse width nLE _{AB} or nLE _{BA} HIGH	see Figs 5 and 8		3.3	0.9	_	ns
	pulse width nCP _{AB} or nCP _{BA} HIGH or LOW	see Figs 5 and 8		3.3	1.1	-	ns
t _{su}	set-up time nA_n before nCP_{AB}^{\uparrow} or nB_n before nCP_{BA}^{\uparrow}	see Figs 7 and 8		+1.3	-0.3	-	ns
	set-up time CP HIGH or LOW nA_n before $nLE_{AB}\downarrow$ or nB_n before $nLE_{BA}\downarrow$	see Figs 7 and 8		1.0	0.3	-	ns
t _h	hold time nA_n after nCP_{AB}^{\uparrow} or nB_n after nCP_{BA}^{\uparrow}	see Figs 7 and 8		+1.3	-0.4	_	ns
	hold time CP HIGH or LOW nA_n after $nLE_{AB}\downarrow$ or nB_n after $nLE_{BA}\downarrow$	see Figs 7 and 8		1.2	0.1	-	ns
f _{max}	maximum clock frequency	see Figs 5 and 8		150	340	_	MHz

Notes

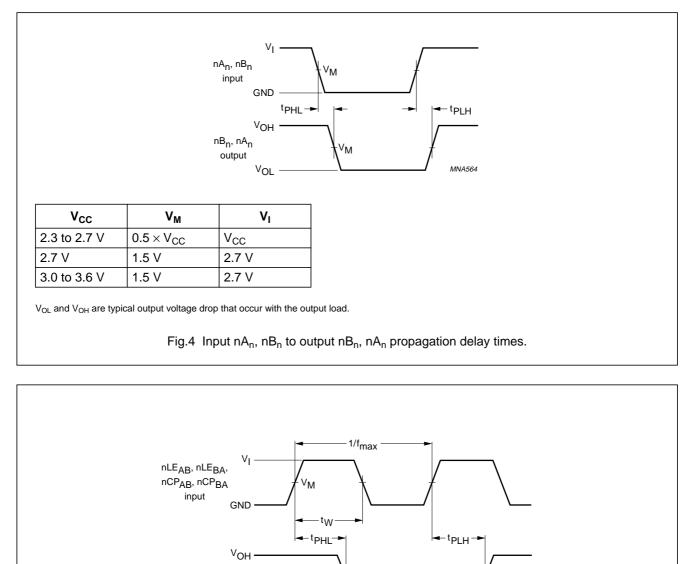
1. All typical values are measured at V_{CC} = 2.5 V and T_{amb} = 25 °C.

2. All typical values are measured at T_{amb} = 25 $^{\circ}C.$

3. All typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 °C.

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AC WAVEFORMS



V _{cc}	V _M	VI
2.3 to 2.7 V	$0.5 \times V_{CC}$	V _{CC}
2.7 V	1.5 V	2.7 V
3.0 to 3.6 V	1.5 V	2.7 V

nA_n, nB_n

output

 V_{OL}

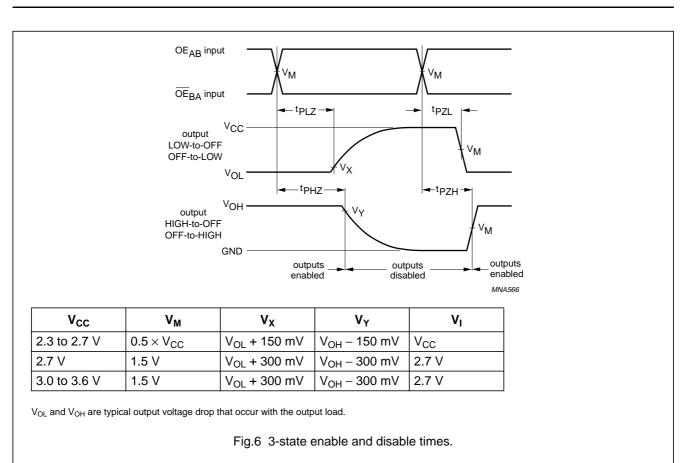
 V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

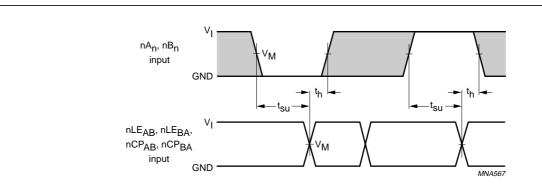
Fig.5 Latch enable input (nLE_{AB}, nLE_{BA}) and clock input (nCP_{AB}, nCP_{BA}) to output propagation delays and their pulse width.

Vм

MNA565

74ALVCH32501





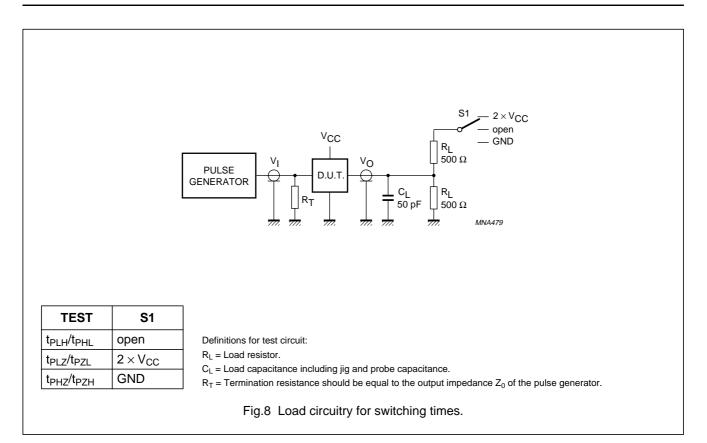
The shaded areas indicate when the input is permitted to change for predictable output performance.

V _{CC}	V _M	VI
2.3 to 2.7 V	$0.5 \times V_{CC}$	V _{CC}
2.7 V	1.5 V	2.7 V
3.0 to 3.6 V	1.5 V	2.7 V

 V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

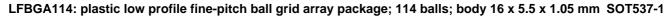
Fig.7 Data set-up and hold times for the nA_n and nB_n inputs to the nLE_{AB} , nLE_{BA} , nCP_{AB} and nCP_{BA} inputs.

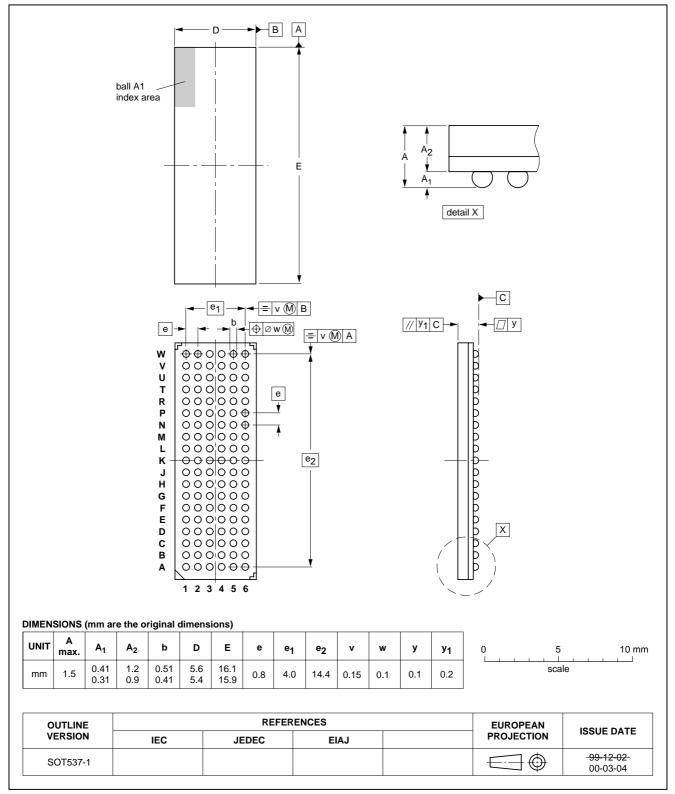
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PACKAGE OUTLINE





74ALVCH32501

SOLDERING

Introduction to soldering surface mount packages

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our *"Data Handbook IC26; Integrated Circuit Packages"* (document order number 9398 652 90011).

There is no soldering method that is ideal for all surface mount IC packages. Wave soldering is not always suitable for surface mount ICs, or for printed-circuit boards with high population densities. In these situations reflow soldering is often used.

Reflow soldering

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several methods exist for reflowing; for example, infrared/convection heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 to 250 °C. The top-surface temperature of the packages should preferable be kept below 230 °C.

Wave soldering

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):
 - larger than or equal to 1.27 mm, the footprint longitudinal axis is preferred to be parallel to the transport direction of the printed-circuit board;
 - smaller than 1.27 mm, the footprint longitudinal axis must be parallel to the transport direction of the printed-circuit board.

The footprint must incorporate solder thieves at the downstream end.

• For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time is 4 seconds at 250 °C. A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

Manual soldering

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to $300 \,^{\circ}$ C.

When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 $^\circ\text{C}.$

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Suitability of surface mount IC packages for wave and reflow soldering methods

PACKAGE	SOLDERING METHOD	
	WAVE	REFLOW ⁽¹⁾
BGA, LFBGA, SQFP, TFBGA	not suitable	suitable
HBCC, HLQFP, HSQFP, HSOP, HTQFP, HTSSOP, SMS	not suitable ⁽²⁾	suitable
PLCC ⁽³⁾ , SO, SOJ	suitable	suitable
LQFP, QFP, TQFP	not recommended ⁽³⁾⁽⁴⁾	suitable
SSOP, TSSOP, VSO	not recommended ⁽⁵⁾	suitable

Notes

- 1. All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the "Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods".
- 2. These packages are not suitable for wave soldering as a solder joint between the printed-circuit board and heatsink (at bottom version) can not be achieved, and as solder may stick to the heatsink (on top version).
- 3. If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
- 4. Wave soldering is only suitable for LQFP, TQFP and QFP packages with a pitch (e) equal to or larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.
- 5. Wave soldering is only suitable for SSOP and TSSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	

Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

LIFE SUPPORT APPLICATIONS

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